



Unit of Materials and Optoelectronic Devices



University of Valencia www.uv.es/umdo



I. Suárez, P.J. Rodríguez-Cantó and J.P. Martínez-Pastor

Current State of the work Eindhoven January 28th 2014



Outline

1-Current Status of the work

- 1.1-Plasmonic amplifiers by using polymers doped with QDs
- 1.2-Photodetectors based on QDs and polymers

2- Next steps and collaborations with other partners

3-Reports

- 3.1-Deliverables
- 3.2-Milestones
- 3.3-Dissemination



Previous (to the review meeting in Brusels)

- Design of plasmonic amplifiers
- Active properties of CdSe QDs, PbS QRs

Last months

- HgTe as an active material
- 2D plasmonic waveguides
- Propagation length in plasmonic waveguides



Active HgTe waveguides



Filling factor (*ff*) implies a trade-off between absorption losses and generated photoluminescence (**PL**)

Pump from the surface



This configuration can solve this trade-off by finding optimal thicknesses

→ High amount of waveguided PL
→ not net amplification yet



Active HgTe waveguides



0.8

0.9

Energy (eV)

1.0

1 1





 α ~20 cm⁻¹



2D Plasmonic waveguides



Au stripes (~10 μm) by UV lift-off process
Covered by active material

Near field characterization:

- 1) Photonic TE mode on the dielectric
- 2) Photonic TE mode on the metal
 - 1) Photonic TM mode on the dielectric
 - 2) Plasmonic TM mode on the metal



Plasmonic waveguides

Method to characterize Propagation length:



LR-SPP $L_p=12.5 \ \mu m$, close to the theoretical (11 μm)



Photodetectors

Milestone 23

Current tasks:

- Enhancement of Responsivity at near-IR of QD-Schottky PD
- Nanogap design under fabrication.

and Voc 10x more at 820 nm.

Photomask for fabricating microgap contacts ordered.



Before (spin-coating) I(V) curves dark PD - Schottky 2 560 nm $P_{i} = 4.4 \, \mu W$ (hJ) R= 0.7 A/W Dr. Blade deposition is being used for 200--2 810 nm 500 nm thickness of layers, but still needing further work for optimization. R= 0.003 A/W Better results are obtained: larger 0.01 0.00 resistivity layers and hence lower reverse Bias (V) bias losses in Schottky diodes. Responsivity



Photodetectors

Milestone 23

Current tasks:

- Enhancement of Responsivity at near-IR of QD-Schottky PD
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- Dr. Blade deposition is being used for 200-500 nm thickness of layers, but still needing further work for optimization.
- Better results are obtained: larger resistivity layers and hence lower reverse bias losses in Schottky diodes. Responsivity and Voc 10x more at 820 nm.





Gain in HgTe QDs

- Improve excitation
- Report sent to to UGENT \rightarrow New samples from UGENT

Plasmonic waveguides

- Propagation length in optimized structures (1D or 2D)
- Set-up to include pumping
- Samples with HgTe QDs

Photodetector

- Nanogap \rightarrow In contact with Victor

Air		
РММА	d ₃	
QD-PMMA	d ₁	
Au	‡ t	
РММА	d ₂	
SiO ₂ 2	μm	
Silicon		



Deliverables and Milestones

	Names of the Milestones	Month	Partner
MS16	Decision on optimized structures for plasmonic amplifiers	12	UVEG
MS17	Synthesis of nanoparticles with gain at 1550nm	12	UGENT
MS18	Demonstration of conductive QD layers with photoconductive properties	15	UVEG
MS19	Demonstration of metal-(lithographic) polymer and QD metal-(lithographic) polymer nanocompo-sites	15	UVEG
MS20	Demonstration and decision on photodetector operation: nano-gap (MIM) vs. Schottky / heterostructure	18	UVEG
MS22	Demonstration of plasmonic amplifiers with optical pumping exhibiting 10 dB gain	21	IMEC
MS23	Operation of QD based photodetector with responsivity > 0.1 A/W	24	UVEG
MS24	Demonstration of SPP amplifiers with electrical injection exhibiting 10dB/cm gain	30	UVEG



	Names of the Deliverables	Month	Partner
D4.1	Designs of plasmonic amplifiers	18	UVEG
D4.2	Report on optical properties of QDs layers and polymer nanocomposites	18	UVEG
D4.3	Designs of plasmonic photodetectors	24	UVEG
D4.4	Report on SPP amplifiers by using QDs	30	IMEC
D4.5	Report on plasmonic photodetectors	33	UVEG
D.7.1	First report on NAVOLCHI dissemination and promotion activities	18	AIT
D.7.2	First report on NAVOLCHI exploitation activities	18	AIT



Dissemination

- Invited talk at ICTON: Will there be Navolchi session?